

30V P-Channel MOSFET



SOP-8

Pin Definition:

- 1. Source
- 2. Source
- 3. Source 4. Gate
- 5, 6, 7, 8. Drain

PRODUCT SUMMARY

V _{DS} (V)	$R_{DS(on)}(m\Omega)$	I _D (A)
-30	60 @ V _{GS} = 10V	-5.3
	90 @ V _{GS} = 4.5V	-4.2

Features

- Advance Trench Process Technology
- High Density Cell Design for Ultra Low On-resistance

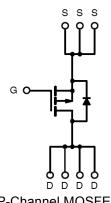
Application

- Load Switch
- PA Switch

Ordering Information

Part No.	Package	Packing
TSM9435CS RF	SOP-8	2.5Kpcs / 13" Reel

Block Diagram



P-Channel MOSFET

Absolute Maximum Rating (Ta = 25°C unless otherwise noted)

Parameter		Symbol	Limit	Unit	
Drain-Source Voltage		V_{DS}	-30	V	
Gate-Source Voltage		V_{GS}	±20	V	
Continuous Drain Current, V _{GS} @4.5V.		I _D	-5.3	Α	
Pulsed Drain Current, V _{GS} @4.5V		I _{DM}	-20	Α	
Continuous Source Current (Diode Con-	duction) ^{a,b}	I _S	-1.9	Α	
Maximum Power Dissipation	Ta = 25°C	Б	2.5	W	
	Ta = 70°C	- P _D	1.3		
Operating Junction Temperature		TJ	+150	°C	
Operating Junction and Storage Tempe	rature Range	T _J , T _{STG} - 55 to +150		°C	

Thermal Performance

Parameter	Symbol	Limit	Unit
Junction to Case Thermal Resistance	R⊖ _{JC}	30	°C/W
Junction to Ambient Thermal Resistance (PCB mounted)	RO _{JA}	50	°C/W

1/6

- a. Pulse width limited by the Maximum junction temperature
- b. Surface Mounted on FR4 Board, $t \le 5$ sec.

Version: B07



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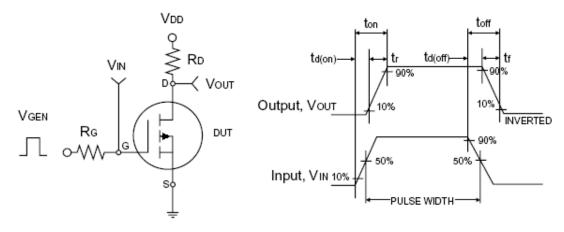


Electrical Specifications

Parameter	Conditions	Symbol	Min	Тур	Max	Unit
Static						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = -250uA$	BV _{DSS}	-30		-	V
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	$V_{GS(TH)}$	-1.0	-1.5	-3.0	V
Gate Body Leakage	$V_{GS} = \pm 20V, V_{DS} = 0V$	I _{GSS}			±100	nA
Zero Gate Voltage Drain Current	$V_{DS} = -24V, V_{GS} = 0V$	I _{DSS}			-1.0	μA
On-State Drain Current ^a	$V_{DS} = -5V, V_{GS} = -10V$	I _{D(ON)}	-6		I	Α
Drain-Source On-State Resistance ^a	$V_{GS} = -10V, I_D = -5.3A$	R _{DS(ON)}	50	60	m0	
Drain-Source On-State Resistance	$V_{GS} = -4.5V$, $I_{D} = -4.2A$	MDS(ON)		75	90	mΩ
Forward Transconductance ^a	$V_{DS} = -15V$, $I_{D} = -5.3A$	g _{fs}	4	7	I	S
Diode Forward Voltage	$I_S = -1.9A$, $V_{GS} = 0V$	V_{SD}		-0.8	-1.3	V
Dynamic ^b				_		
Total Gate Charge	$V_{DS} = -15V, I_{D} = -5.3A,$	Q_g		9.52		
Gate-Source Charge	$V_{DS} = -10V$, $I_D = -5.3A$,	Q_gs		3.43		nC
Gate-Drain Charge	V _{GS} = -10 V	Q_{gd}		1.71		
Input Capacitance	\/ - 45\/ \/ - 0\/	C _{iss}		551.57	-	
Output Capacitance	$V_{DS} = -15V, V_{GS} = 0V,$ f = 1.0MHz	C _{oss}		90.96	I	pF
Reverse Transfer Capacitance	1 - 1.0IVIM2	C _{rss}		60.79	I	
Switching ^c						
Turn-On Delay Time	15) D 450	t _{d(on)}		10.8		
Turn-On Rise Time	$V_{DD} = -15V, R_L = 15\Omega,$	t _r		2.33	1	nC
Turn-Off Delay Time	$I_D = -1A$, $V_{GEN} = -10V$,	t _{d(off)}		22.53		nS
Turn-Off Fall Time	$R_G = 6\Omega$	t _f		3.87	-	

Notes:

- a. pulse test: PW \leq 300µS, duty cycle \leq 2% b. For DESIGN AID ONLY, not subject to production testing.
- b. Switching time is essentially independent of operating temperature.



Switching Test Circuit

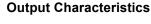
Switchin Waveforms

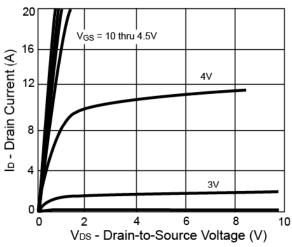


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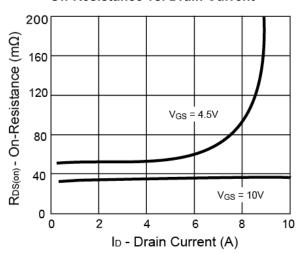


Electrical Characteristics Curve (Ta = 25°C, unless otherwise noted)

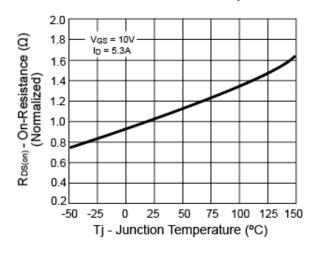




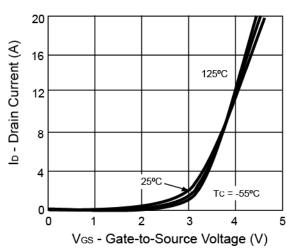
On-Resistance vs. Drain Current



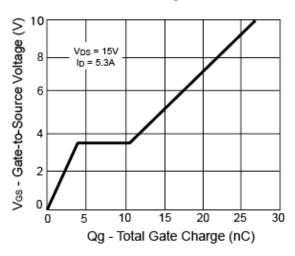
On-Resistance vs. Junction Temperature



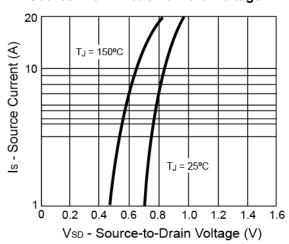
Transfer Characteristics



Gate Charge



Source-Drain Diode Forward Voltage



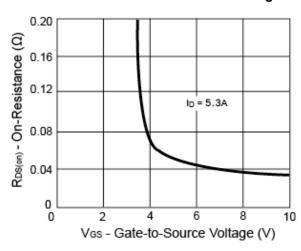


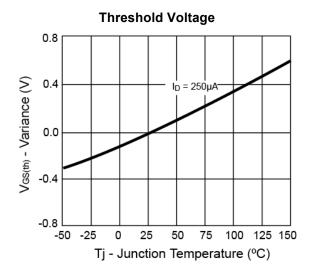




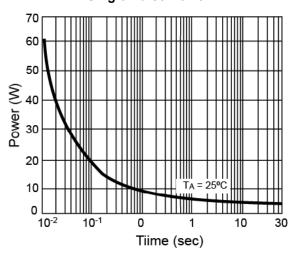
Electrical Characteristics Curve (Ta = 25°C, unless otherwise noted)

On-Resistance vs. Gate-Source Voltage

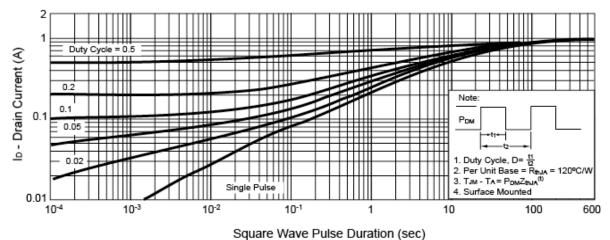




Single Pulse Power



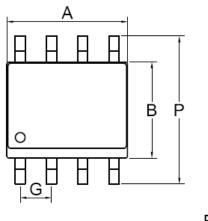
Normalized Thermal Transient Impedance, Junction-to-Ambient

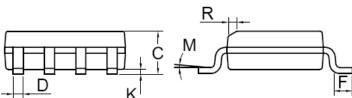






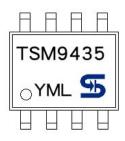
SOP-8 Mechanical Drawing





SOP-8 DIMENSION					
DIM	MILLIMETERS		INCHES		
DIIVI	MIN	MAX	MIN	MAX.	
Α	4.80	5.00	0.189	0.196	
В	3.80	4.00	0.150	0.157	
С	1.35	1.75	0.054	0.068	
D	0.35	0.49	0.014	0.019	
F	0.40	1.25	0.016	0.049	
G	1.27	1.27BSC		BSC	
K	0.10	0.25	0.004	0.009	
М	0°	7°	0°	7°	
Р	5.80	6.20	0.229	0.244	
R	0.25	0.50	0.010	0.019	

Marking Diagram



Y = Year Code

M = Month Code

(A=Jan, B=Feb, C=Mar, D=Apl, E=May, F=Jun, G=Jul, H=Aug, I=Sep, J=Oct, K=Nov, L=Dec)

L = Lot Code



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